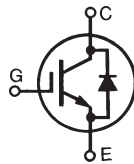


GenX3™ 600V IGBT with Diode

IXGK64N60B3D1 IXGX64N60B3D1

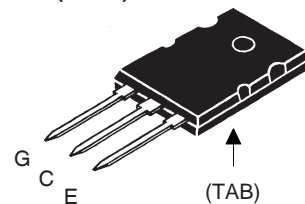
Medium speed low V_{sat} PT IGBTs 5-40 kHz switching



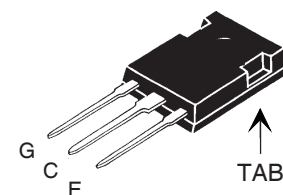
$V_{CES} = 600V$
 $I_{C110} = 64A$
 $V_{CE(sat)} \leq 1.8V$
 $t_{fi(typ)} = 88ns$

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	600	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C110}	$T_C = 110^\circ C$	64	A
I_{CM}	$T_C = 25^\circ C$, 1ms	400	A
SSOA	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 3\Omega$	$I_{CM} = 200$	A
(RBSOA)	Clamped inductive load @ $V_{CE} \leq 600V$		
P_c	$T_C = 25^\circ C$	460	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
M_d	Mounting torque (TO-264)	1.13 / 10	Nm/lb.in.
F_c	Mounting force (PLUS247)	20..120 / 4.5..27	N/lb.
T_L	Maximum lead temperature for soldering	300	$^\circ C$
T_{SOLD}	1.6mm (0.062 in.) from case for 10s	260	$^\circ C$
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS247 (IXGX)



G = Gate C = Collector
 E = Emitter TAB = Collector

Features

- Optimized for low conduction and switching losses
- Square RBSOA
- Anti-parallel ultra fast diode
- International standard packages

Advantages

- High power density
- Low gate drive requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0V$ $T_J = 125^\circ C$			700 μA 2.5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 50A$, $V_{GE} = 15V$, Note 1	1.59	1.80	V

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 50A, V_{CE} = 10V$, Note 1	38	64	S
C_{ies}	$V_{CE} = 25V, V_{GE} = 0V, f = 1MHz$		4750	pF
C_{oes}			260	pF
C_{res}			65	pF
Q_g	$I_C = 50A, V_{GE} = 15V, V_{CE} = 0.5 \cdot V_{CES}$		168	nC
Q_{ge}			28	nC
Q_{gc}			61	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ C$ $I_C = 50A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 3\Omega$		25	ns
t_{ri}			41	ns
E_{on}			1.5	mJ
$t_{d(off)}$			138	ns
t_{fi}			88	150 ns
E_{off}			1.0	1.9 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ C$ $I_C = 50A, V_{GE} = 15V$ $V_{CE} = 480V, R_G = 3\Omega$		24	ns
t_{ri}			40	ns
E_{on}			2.70	mJ
$t_{d(off)}$			195	ns
t_{fi}			131	ns
E_{off}			1.95	mJ
R_{thJC}				0.27 °C/W
R_{thCS}		0.15		°C/W

Reverse Diode (FRED)

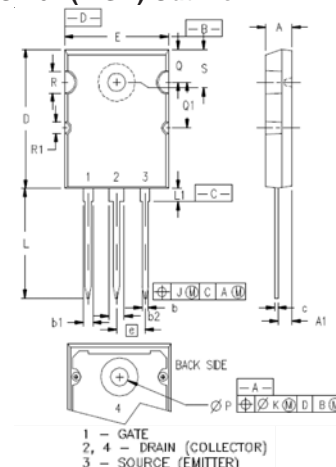
Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 60A, V_{GE} = 0V$, Note 1 $T_J = 150^\circ C$		1.4	2.1 V
I_{RM}	$I_F = 60A, V_{GE} = 0V$, $-di_F/dt = 100A/\mu s, V_R = 100V$ $T_J = 100^\circ C$		8.3	A
t_{rr}	$I_F = 1A, -di/dt = 200A/\mu s, V_R = 30V$		35	ns
R_{thJC}				1.35 °C/W

Note 1: Pulse test, $t \leq 300\mu s$; duty cycle, $d \leq 2\%$.

IXYS reserves the right to change limits, test conditions, and dimensions.

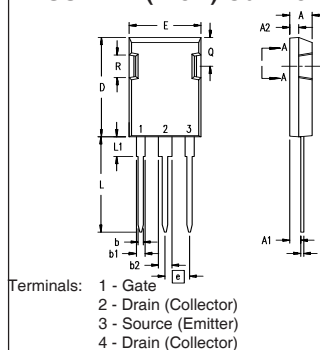
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-264 (IXGK) Outline



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.185	0.209	4.70	5.31
A1	0.102	0.118	2.59	3.00
b	0.037	0.055	0.94	1.40
b1	0.087	0.102	2.21	2.59
b2	0.110	0.126	2.79	3.20
c	0.017	0.029	0.43	0.74
D	1.007	1.047	25.58	26.59
E	0.760	0.799	19.30	20.29
e	.215 BSC		5.46 BSC	
J	0.000	0.010	0.00	0.25
K	0.000	0.010	0.00	0.25
L	0.779	0.842	19.79	21.39
L1	0.087	0.102	2.21	2.59
ØP	0.122	0.138	3.10	3.51
Q	0.240	0.256	6.10	6.50
Q1	0.330	0.346	8.38	8.79
ØR	0.155	0.187	3.94	4.75
ØR1	0.085	0.093	2.16	2.36
S	0.243	0.253	6.17	6.43

PLUS247™ (IXGX) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics
@ 25°C

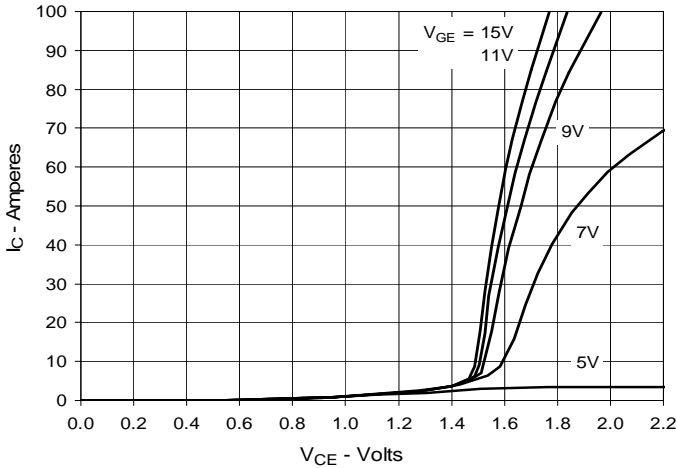


Fig. 2. Extended Output Characteristics
@ 25°C

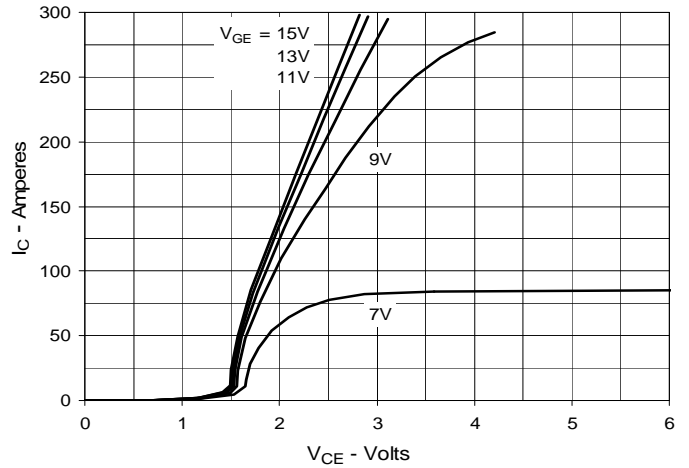


Fig. 3. Output Characteristics
@ 125°C

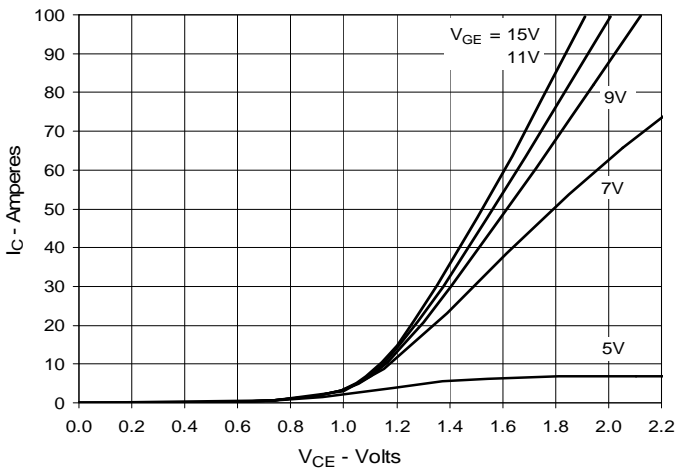


Fig. 4. Dependence of VCE(sat) on Junction Temperature

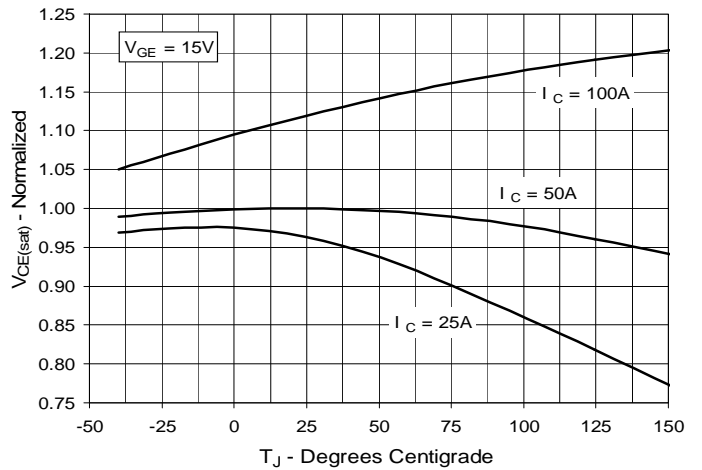


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

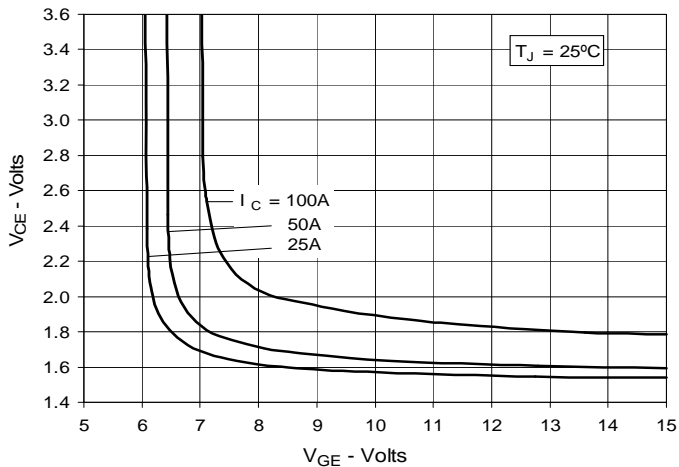


Fig. 6. Input Admittance

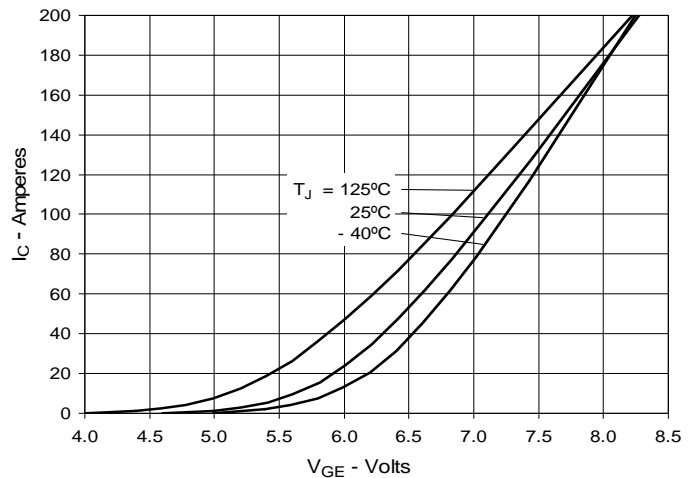


Fig. 7. Transconductance

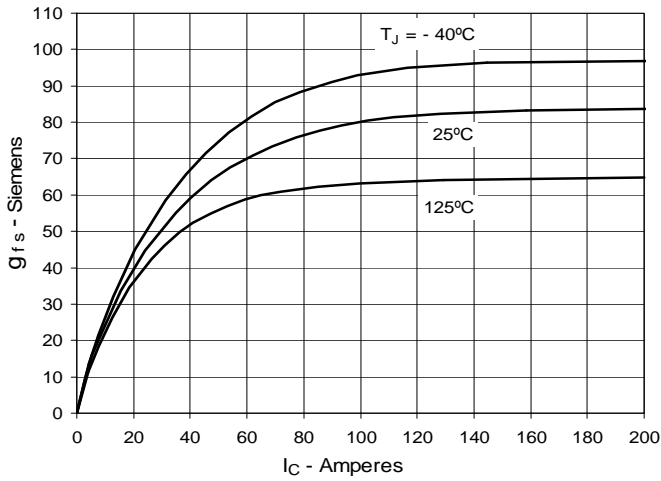


Fig. 8. Gate Charge

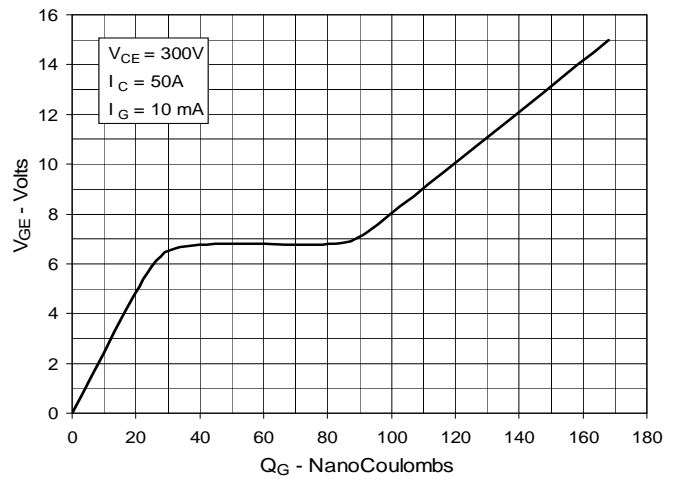


Fig. 9. Reverse-Bias Safe Operating Area

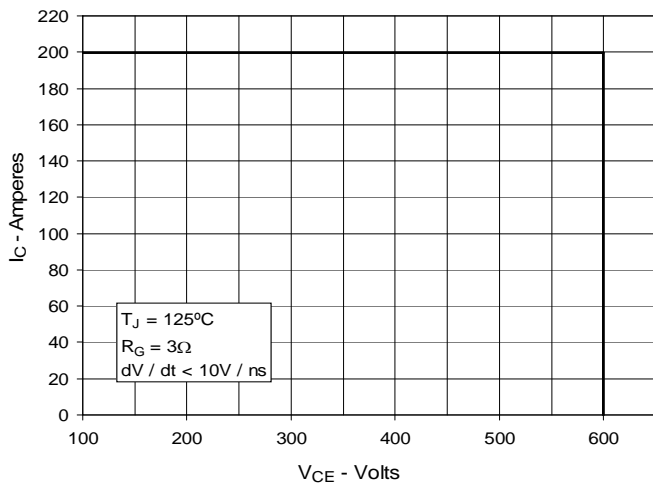


Fig. 10. Capacitance

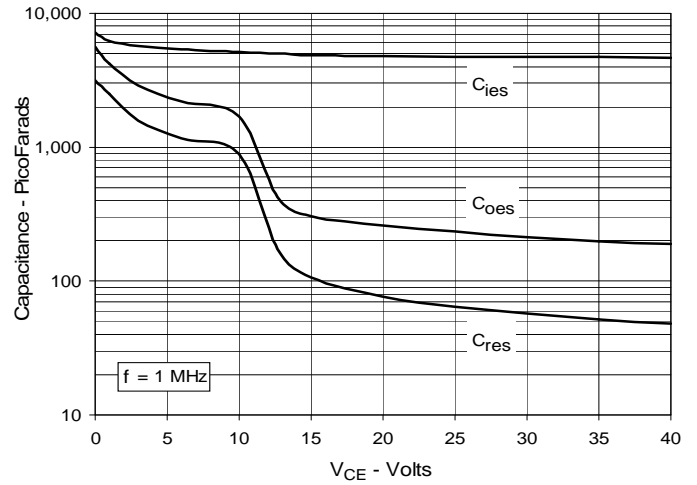


Fig. 11. Maximum Transient Thermal Impedance

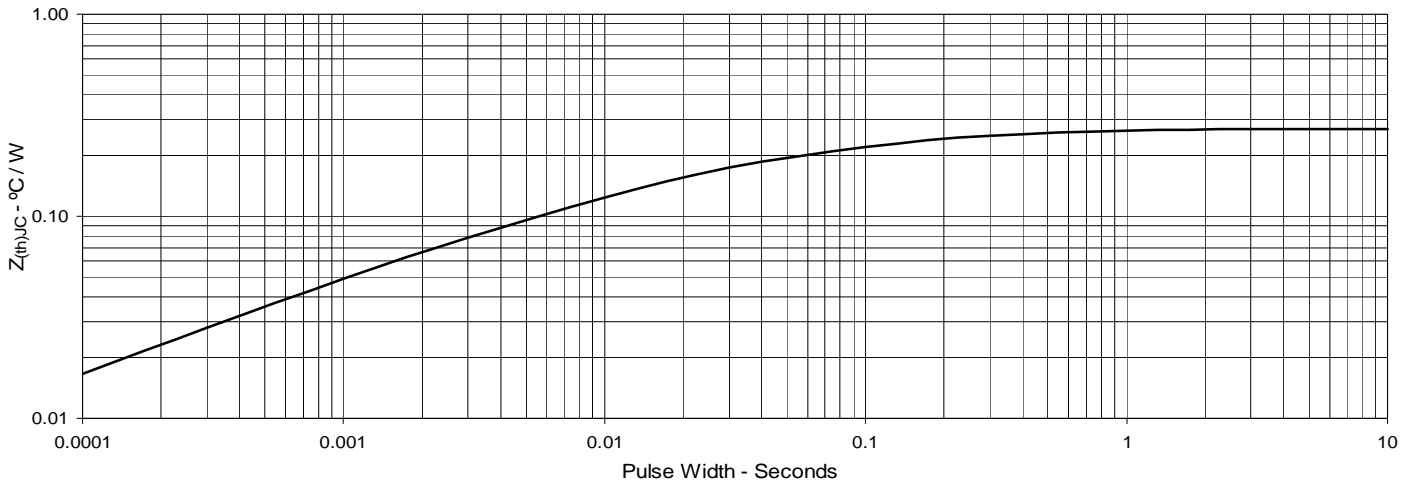


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

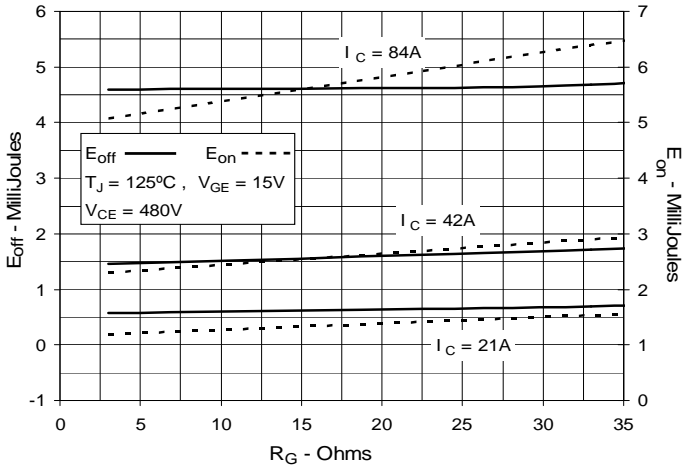


Fig. 13. Inductive Switching Energy Loss vs. Junction Temperature

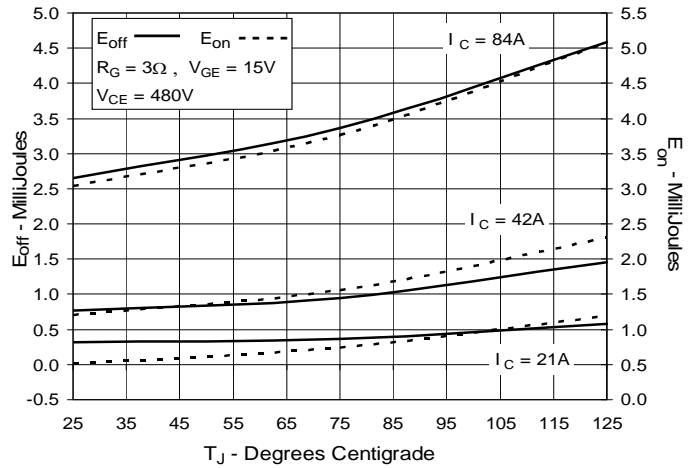


Fig. 14. Inductive Switching Energy Loss vs. Collector Current

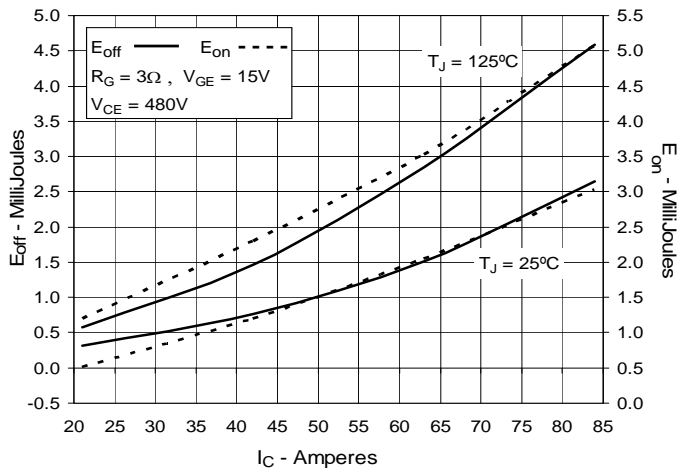


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

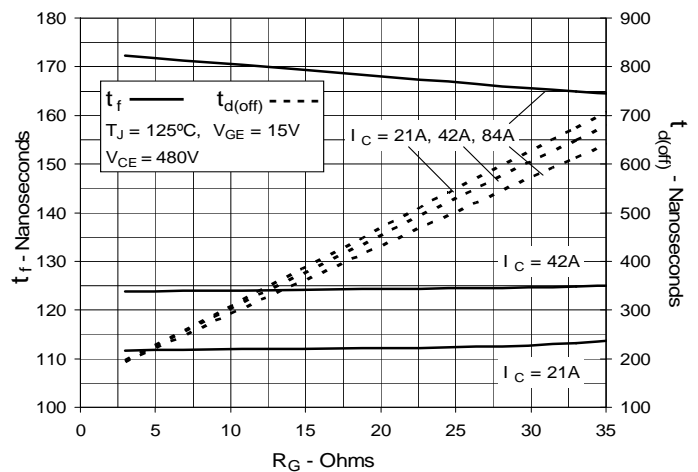


Fig. 16. Inductive Turn-off Switching Times vs. Junction Temperature

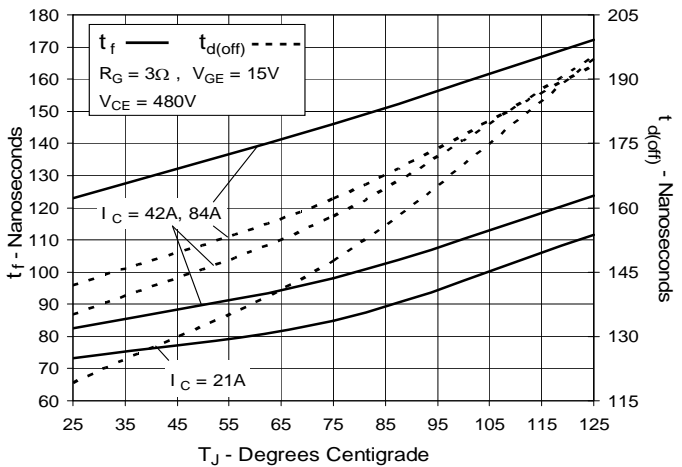


Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

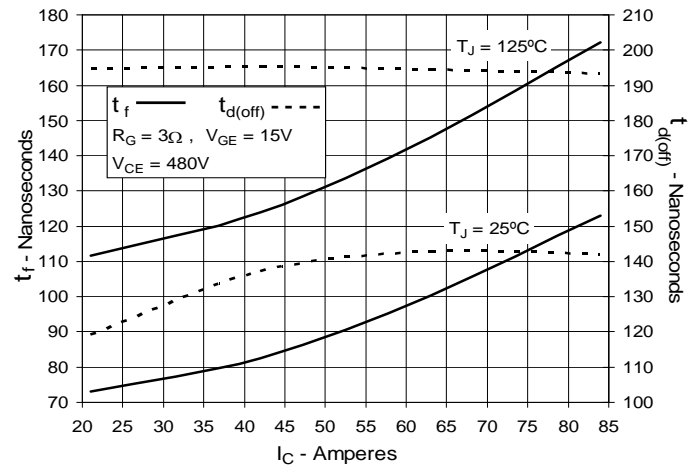


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

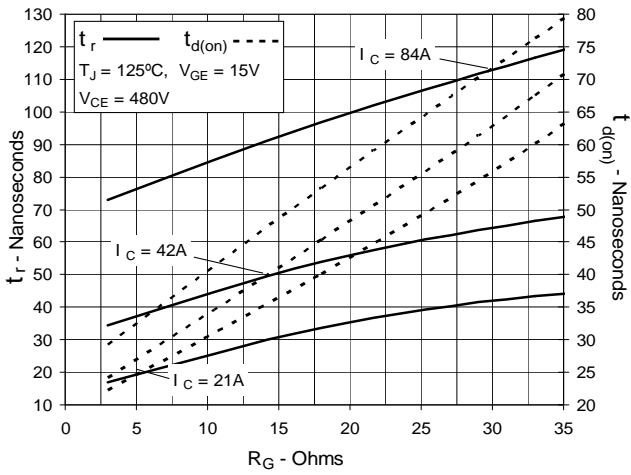


Fig. 19. Inductive Turn-on Switching Times vs. Junction Temperature

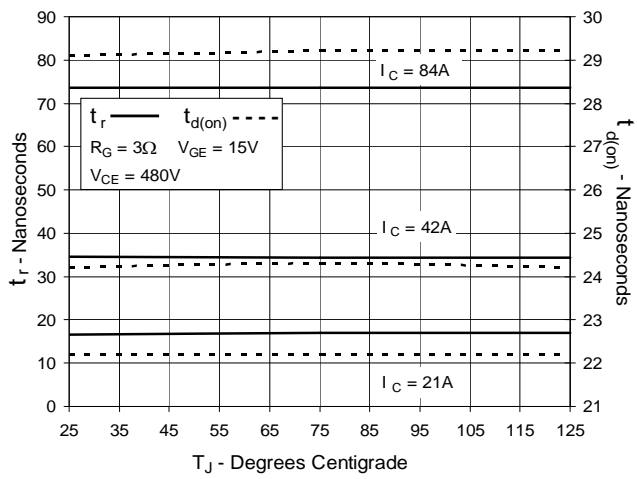
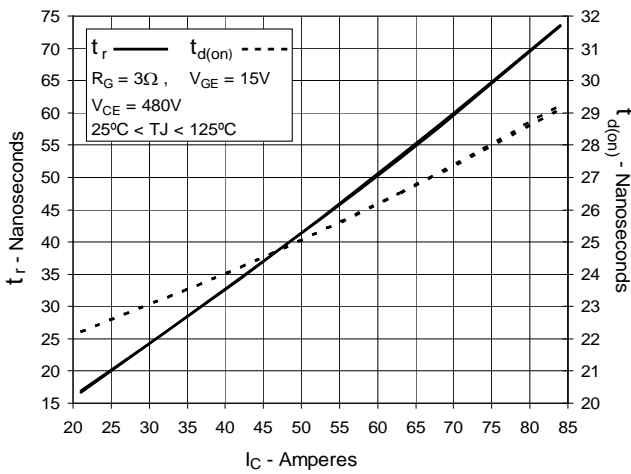


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current



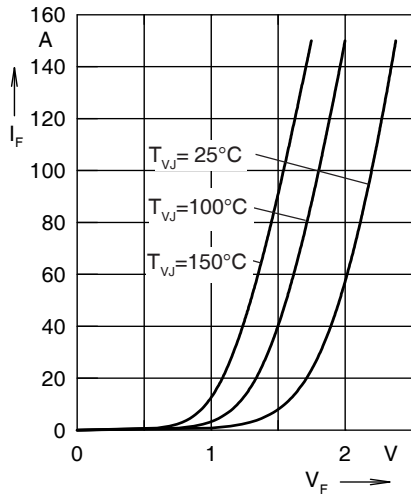


Fig. 21. Forward current I_F versus V_F

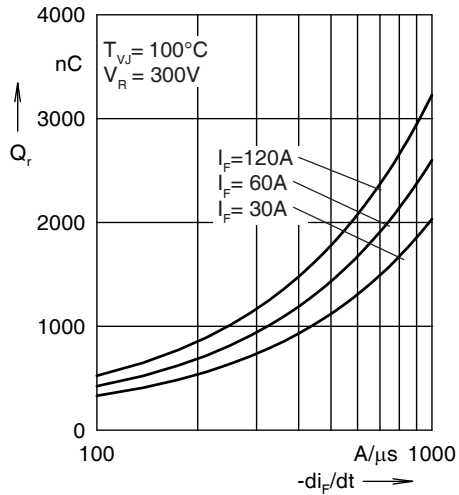


Fig. 22. Reverse recovery charge Q_r versus $-di_F/dt$

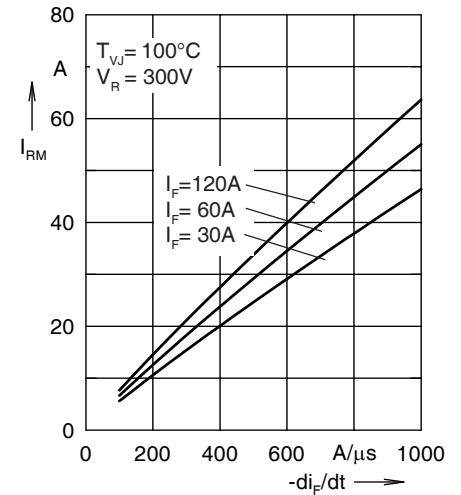


Fig. 23. Peak reverse current I_{RM} versus $-di_F/dt$

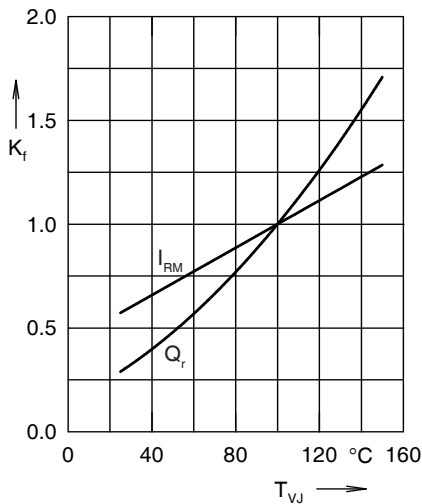


Fig. 24. Dynamic parameters Q_r , I_{RM} versus T_{VJ}

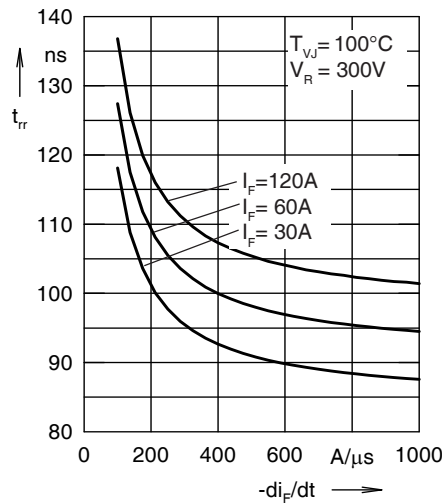


Fig. 25. Recovery time t_{tr} versus $-di_F/dt$

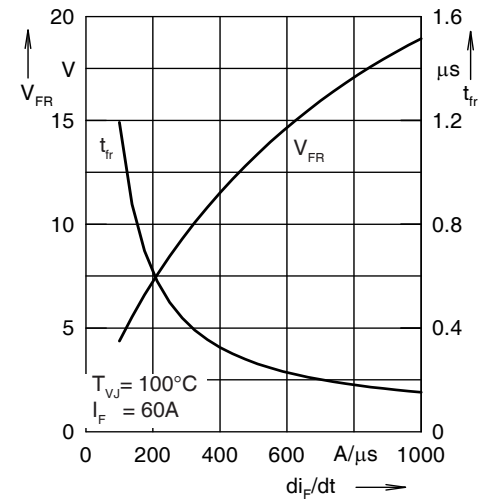


Fig. 26. Peak forward voltage V_{FR} and t_{tr} versus di_F/dt

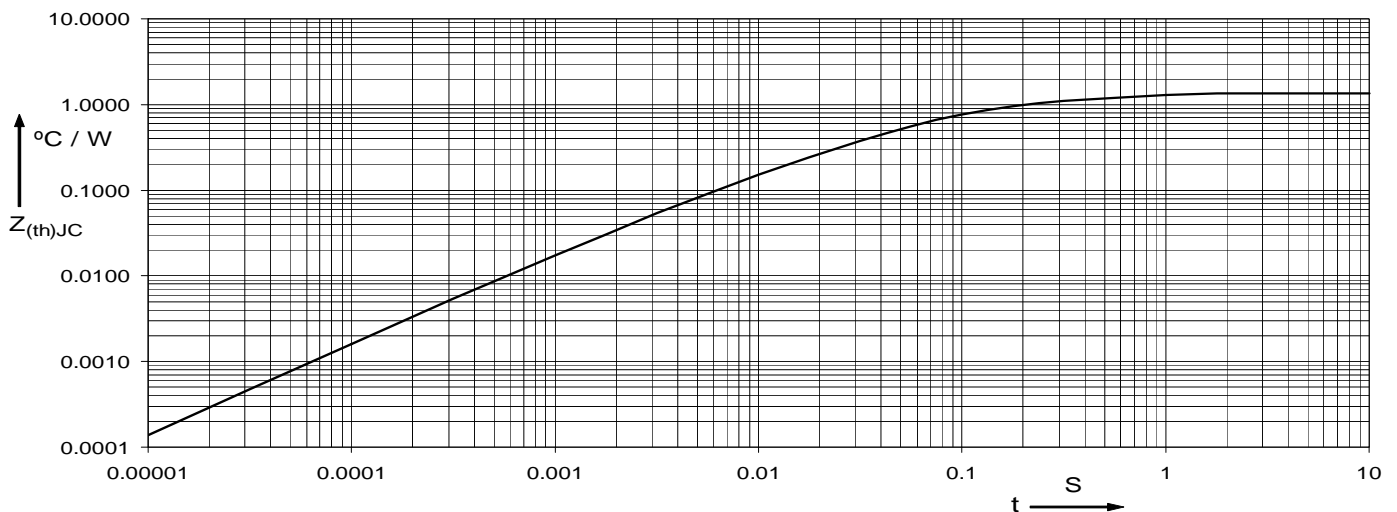


Fig. 27. Maximum transient thermal impedance junction to case (for diode)